

Description

The PS2401A-1, -2, -3, and -4 series are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon photo transistor. Each is mounted in a dual in-line package.

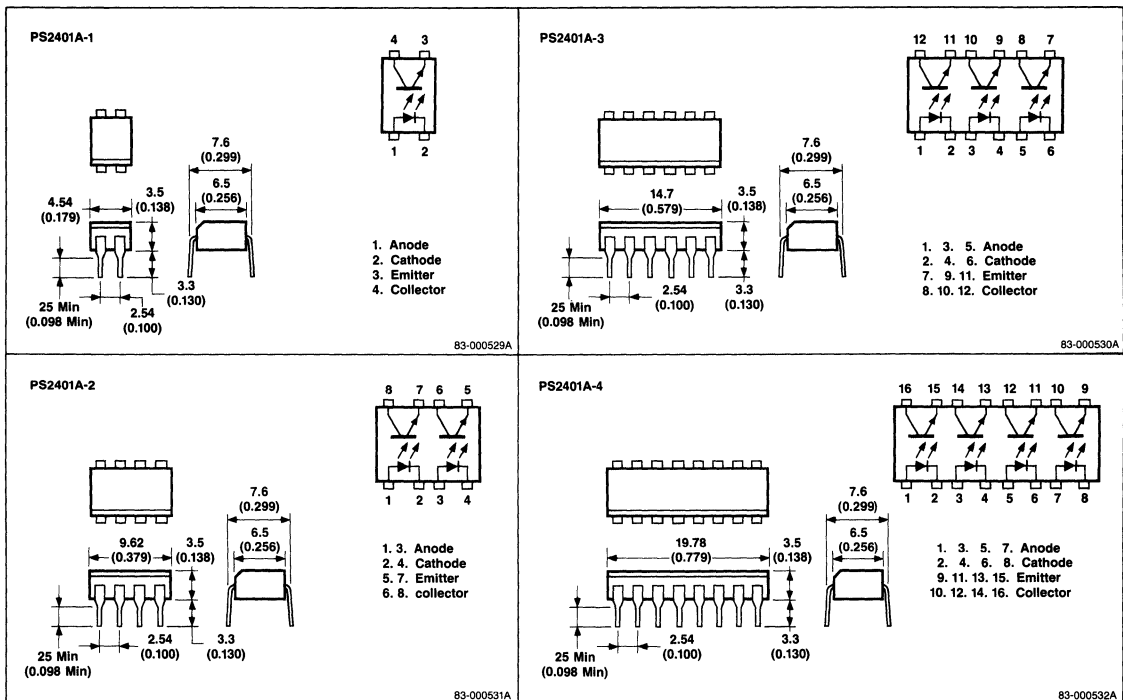
Features

- Small package size
- Isolated channels
- High isolation voltage: 5000V_{AC} rating
- High transfer ratio: 300 % typ
- High speed switching: $t_r, t_f = 3\mu s$ typ
- Low cost

Applications

- Interface circuit for various instrumentations, control equipment
- AC line digital logic: isolate high voltage transients
- Digital logic: eliminate spurious ground loops
- Twisted pair line receiver: eliminate ground loop pick-up
- Telephone/telegraph line receiver: isolate high voltage transients
- High frequency power supply: feedback control, maintain floating ground
- Relay contact monitor: isolate floating grounds and transients
- Power supply monitor: isolate transients and ground systems

Package Dimensions



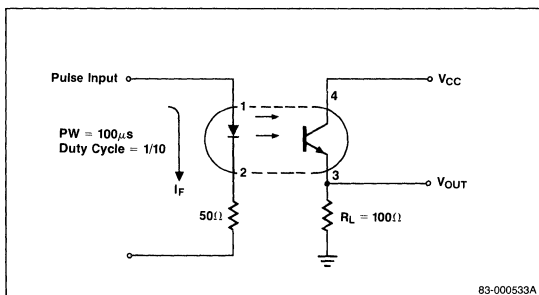
Absolute Maximum Ratings

$T_A = +25^\circ\text{C}$

Diode	
Reverse Voltage, V_R	6.0V
Forward Current (DC), I_F	80mA
Power Dissipation, P_D	150mW
Peak Forward Current (300 μ s, 2% duty cycle), I_F (peak)	3A
Transistor	
Collector to Emitter Voltage, V_{CE0}	40V
Emitter to Collector Voltage, V_{ECO}	7V
Collector Current, I_C	100mA
Power Dissipation, P_D	150mW
Isolation Voltage ¹ , BV	5000V _{AC}
Storage Temperature, T_{STG}	-55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
Operating Temperature, T_{OPT}	-55 $^\circ\text{C}$ to +100 $^\circ\text{C}$
Lead Temperature (Soldering 10s), T_{SOL}	260 $^\circ\text{C}$
Total Power Dissipation, P_T	250mW

- Notes:**
1. Measuring Conditions: AC voltage for 1 min at $T_A = +25^\circ\text{C}$, RH = 60%.
 2. CTR rank: (PS2401A-1 only) K: 300% to 600%, L: 200% to 400%, M: 80% to 240%.
 3. Test circuit for switching time.

Test circuit for switching time



Electrical Characteristics

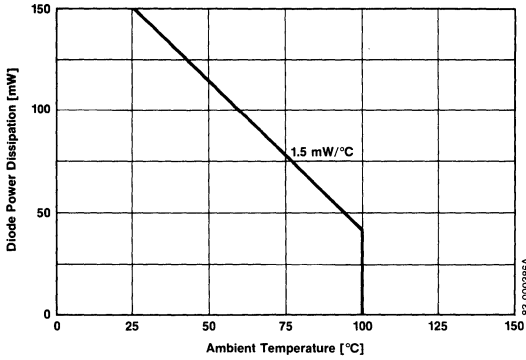
$T_A = +25^\circ\text{C}$

Parameter	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Diode						
Forward Voltage	V_F	1.1	1.4		V	$I_F = 10\text{mA}$
Reverse Current	I_R			5	μA	$V_R = 5\text{V}$
Junction Capacitance	C		50		pF	$V = 0$, $f = 1.0\text{MHz}$
Transistor						
Collector to Emitter Dark Current	I_{CE0}			50	nA	$V_{CE} = 10\text{V}$, $I_F = 0$
Collector to Emitter Dark Current	I_{CE0}			100	nA	$V_{CE} = 40\text{V}$, $I_F = 0$
Collector to Emitter Breakdown Voltage	BV_{CE0}	40	60		V	$I_C = 1\text{mA}$, $I_B = 0$
Emitter to Collector Breakdown Voltage	BV_{ECO}	7	9		V	$I_E = 100\mu\text{A}$, $I_B = 0$
Coupled Current Transfer Ratio ²	CTR (I_C/I_F)	80		600	%	$I_F = 10\text{mA}$, $V_{CE} = 5.0\text{V}$
Collector Saturation Voltage	$V_{CE(sat)}$			0.3	V	$I_F = 10\text{mA}$, $I_C = 2.0\text{mA}$
Isolation Resistance	R_{1-2}	10^{11}			Ω	$V_{IN-OUT} = 1.0\text{kV}$
Isolation Capacitance	C_{1-2}		0.5		pF	$V = 0$, $f = 1.0\text{MHz}$
Rise Time ³	t_r		3		μs	$V_{CC} = 10\text{V}$, $I_C = 2\text{mA}$, $R_L = 100\Omega$
Fall Time ³	t_f		3		μs	$V_{CC} = 10\text{V}$, $I_C = 2\text{mA}$, $R_L = 100\Omega$

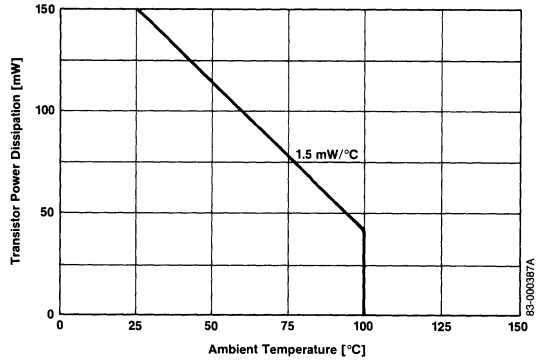
Typical Characteristics

$T_A = +25^\circ\text{C}$

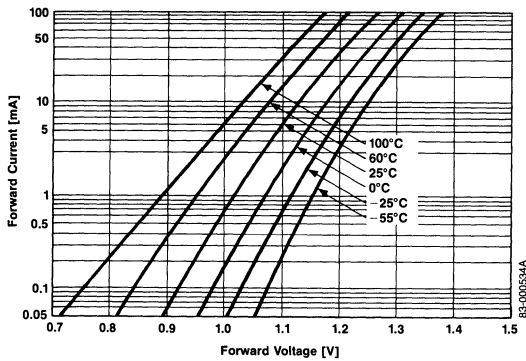
Diode Power Dissipation vs Ambient Temperature



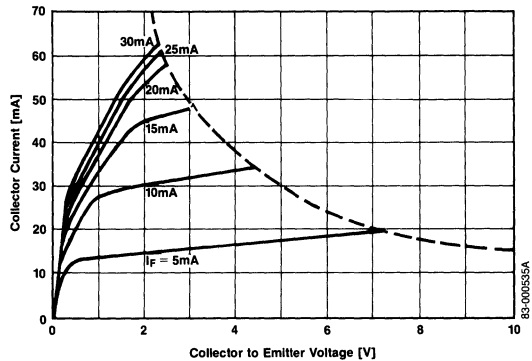
Transistor Power Dissipation vs Ambient Temperature



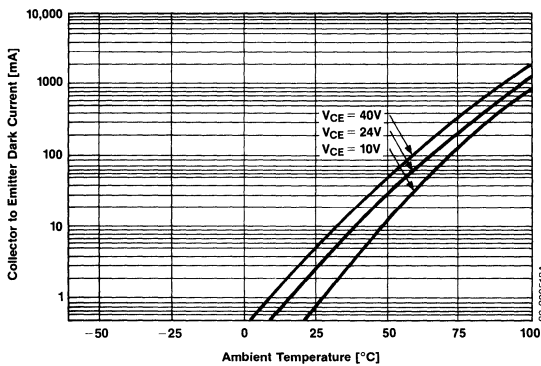
Forward Current vs Forward Voltage



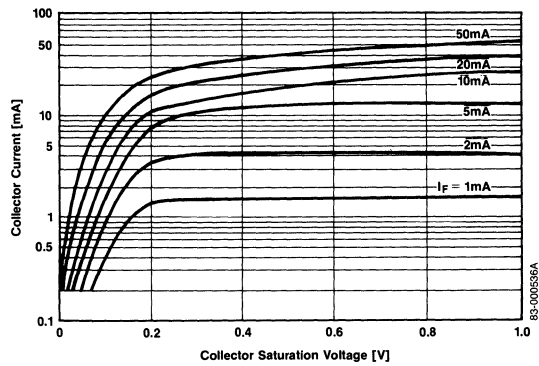
Collector Current vs Collector to Emitter Voltage



Collector to Emitter Dark Current vs Ambient Temperature



Collector Current vs Collector Saturation Voltage



5

Typical Characteristics (cont)

$T_A = +25^\circ\text{C}$

